

# Supporting Information:

## Particle-Particle Random Phase Approximation for Predicting Correlated Excited States of Point Defects

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# 1 Details about geometry optimizations

We optimized the ground-state equilibrium geometries of point defect systems using density functional theory<sup>S1,S2</sup> (DFT) and the plane-wave pseudopotential method, as implemented in the Quantum ESPRESSO package,<sup>S3,S4</sup> by minimizing the nuclear forces below the threshold of 0.01 eV Å<sup>-1</sup>. Our study involved Kohn-Sham DFT calculations for the singlet ground states of point defect systems, specifically the <sup>1</sup>A<sub>1g</sub> ground state of VO in MgO and the <sup>1</sup>A<sub>1</sub> ground state of C<sub>B</sub>C<sub>N</sub> in 2D-hBN. For VC in diamond, two separate DFT calculations were performed to obtain the equilibrium geometry with the D<sub>2d</sub> and the T<sub>d</sub> symmetry. To obtain the geometry with the T<sub>d</sub> symmetry, each of the three degenerate *t*<sub>2</sub> KS orbitals was enforced to accommodate 2/3 of an electron. We used SG15 ONCV norm-conserving pseudopotentials<sup>S5,S6</sup> and the PBE<sup>S7</sup> functional with the plane-wave energy cutoff setting to 60 Ry.

# 2 Excitation energies of defects obtained from ppRPA

Table S1: Vertical excitation energies of VC in diamond obtained from ppRPA@PBE and ppRPA@B3LYP with supercell models containing 63 and 215 atoms. (*O*, *V*) means that *O* occupied orbitals and *V* virtual orbitals were used in the active space. The geometry of the <sup>1</sup>A<sub>1</sub> ground state and cc-pVDZ basis set were used. All values are in eV.

	ppRPA@PBE		ppRPA@B3LYP	
	<sup>1</sup> T <sub>2</sub> (D <sub>2d</sub> )	<sup>1</sup> T <sub>2</sub> (T <sub>d</sub> )	<sup>1</sup> T <sub>2</sub> (D <sub>2d</sub> )	<sup>1</sup> T <sub>2</sub> (T <sub>d</sub> )
supercell 63	1.43	1.38	1.70	1.62
supercell 215 (200, 200)	1.91	1.78	2.30	2.14
supercell 215 (250, 250)	1.84	1.71	2.22	2.05
supercell 215 (300, 300)	1.81	1.67	2.19	2.01
supercell 215 (400, 400)	1.78	1.64	2.15	1.96

Table S2: Vertical excitation energies of VO in MgO obtained from ppRPA@PBE and ppRPA@B3LYP with supercell models containing 63 and 215 atoms. ( $O$ ,  $V$ ) means that  $O$  occupied orbitals and  $V$  virtual orbitals were used in the active space. The geometry of the  $^1A_{1g}$  ground state and cc-pVDZ basis set were used. All values are in eV.

	ppRPA@PBE		ppRPA@B3LYP	
	$^1T_{1u}$	$^3T_{1u}$	$^1T_{1u}$	$^3T_{1u}$
supercell 63	5.05	3.91	5.23	3.97
supercell 215 (200, 200)	4.75	3.52	4.90	3.49
supercell 215 (250, 250)	4.76	3.53	4.92	3.51
supercell 215 (300, 300)	4.80	3.57	4.98	3.56
supercell 215 (400, 400)	4.82	3.60	5.01	3.60

Table S3: Vertical excitation energies of  $C_B C_N$  in h-BN obtained from ppRPA\*@PBE and ppRPA\*@B3LYP with the supercell model containing 128 atoms. ( $O$ ,  $V$ ) means that  $O$  occupied orbitals and  $V$  virtual orbitals were used in the active space. The geometry of the  $^1A_1$  ground state and cc-pVDZ basis set were used. All values are in eV.

	ppRPA@PBE	ppRPA@B3LYP
	$^1A_1$	$^1A_1$
supercell 128 (200, 200)	3.76	4.51
supercell 128 (250, 250)	3.76	4.52
supercell 128 (300, 300)	3.77	4.52
supercell 128 (400, 400)	3.77	4.52

### 3 Basis set convergence

Vertical excitation energies of VO in MgO obtained from ppRPA@PBE and ppRPA@B3LYP with cc-pVDZ and cc-pVTZ basis sets<sup>S8</sup> and the supercell model containing 63 atoms are tabulated in Table. S4. It shows that excitation energies obtained from ppRPA with cc-pVDZ and cc-pVTZ basis sets are very similar. The differences between the results of ppRPA using cc-pVDZ and cc-pVTZ are smaller than 0.02 eV. Thus, the cc-pVDZ basis set is used for ppRPA calculations in this work.

Table S4: Vertical excitation energies of VO in MgO obtained from ppRPA@PBE and ppRPA@B3LYP with cc-pVTZ basis set. ( $O$ ,  $V$ ) means that  $O$  occupied orbitals and  $V$  virtual orbitals were used in the active space. The geometry of the  ${}^1A_{1g}$  ground state and the supercell model containing 63 atoms were used. All values are in eV.

	ppRPA@PBE cc-pVDZ		ppRPA@PBE cc-pVTZ	
	${}^1T_{1u}$	${}^3T_{1u}$	${}^1T_{1u}$	${}^3T_{1u}$
(200, 200)	5.05	3.91	5.03	3.89
(300, 300)	5.05	3.91	5.03	3.89
	ppRPA@B3LYP cc-pVDZ		ppRPA@B3LYP cc-pVTZ	
	${}^1T_{1u}$	${}^3T_{1u}$	${}^1T_{1u}$	${}^3T_{1u}$
(200, 200)	5.24	3.96	5.23	3.96
(300, 300)	5.23	3.96	5.22	3.97

### 4 Excitation energies of defect systems obtained from TDDFT

Table S5: Vertical excitation energies of VC in diamond obtained from TDDFT@PBE and TDDFT@B3LYP with supercell models containing 63 and 215 atoms. The geometry of the  $^1A_1$  ground state of  $D_{2d}$  symmetry was used. All values are in eV.

	$^1T_2$
TDDFT@PBE (supercell 63)	1.01
TDDFT@PBE (supercell 215)	1.19
TDDFT@B3LYP (supercell 63)	1.07
TDDFT@B3LYP (supercell 215)	1.30

Table S6: Vertical excitation energies of VO in MgO obtained from TDDFT@PBE and TDDFT@B3LYP with supercell models containing 63 and 215 atoms. The geometry of the  $^1A_{1g}$  ground state was used. All values are in eV.

	$^1T_{1u}$	$^3T_{1u}$
TDDFT@PBE (supercell 63)	5.02	3.79
TDDFT@PBE (supercell 215)	3.86	3.29
TDDFT@B3LYP (supercell 63)	5.35	3.92
TDDFT@B3LYP (supercell 215)	4.60	3.57

Table S7: Vertical excitation energies of  $C_B C_N$  in h-BN obtained from TDDFT@PBE and TDDFT@B3LYP with the supercell model containing 128 atoms. The geometry of the  $^1A_1$  ground state was used. All values are in eV.

	$^1A_1$
TDDFT@PBE (supercell 128)	4.03
TDDFT@B3LYP (supercell 128)	4.63

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